



LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO.:	APPLICATION NO.:
	4717-10000	10/784,016
	APPLICANT:	
	Bruno GHYSELEN et al.	
	FILING DATE:	GROUP:
	February 20, 2004	2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TT	AA	5,461,243	10/1995	Ek et al.	257	190	
TT	AB	6,352,942 B1	3/2002	Luan et al.	438	770	
TT	AC	6,100,166	8/2000	Sakaguchi et al.	438	455	
	AD						
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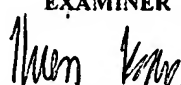
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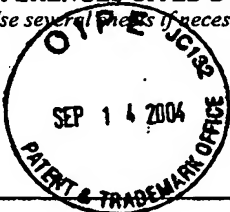
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ							
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TT	AM	B. Holländer et al., "Strain relaxation of pseudomorphic Si _x Ge _{1-x} /Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) 357-367 (2001)
TT	AN	K.D. Hobart et al. "Complaint Substrates: A Comparative Study of the Relaxation Mechanisms of Strained Films Bonded to High and Low Viscosity Oxides", Electronic Materials, Vol. 29, No. 7, pp. 897-900 (2000)
TT	AO	Friedrich Schäffler, "High-mobility Si and Ge structures", Semicond. Sci. Technol., Vol. 12, pp.1515-1548 (1997)
TT	AP	Q. Y. Tong et al "Extracts of "Semi-conductor on wafer bonding", Science and Technology, Interscience Technology, Wiley Interscience publication, Johnson Wiley & Sons, Inc.
TT	AQ	J.P. Collinge, "Silicon-on-insulator technology", Materials to VLSI, 2nd Edition", Kluwer Academic Publisher, pp. 50-51.

EXAMINER 	DATE CONSIDERED 03/09/2005
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
TT	AA	5,882,987	3/1999	Sirikrishnan	438	458		
TT	AB	2002/0072130 A1	6/2002	Cheng et al.	438	10		
TT	AC	2002/0168864 A1	11/2002	Cheng et al.	438	725		
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TT	AE	2003/0013305 A1	1/2003	Sugii et al.	438	689		
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
TT	AJ	EP 1 248 294 A2	10/2002	Europe			X	
TT	AK	WO 99/53539	10/1999	PCT			X	
TT	AL	WO/0243153A1 (w/English Abstract)	5/2002	PCT			X	
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TT	AQ	S. Mantl et al., "Strain relaxation of epitaxial SGe layers on Si(100) improved by hydrogen implantation" Nuclear Instruments and Methods in Physics Research , Vol. 147, No. 1-4, pp. 29-34 (1999)						
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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TT	AA	6,059,895	5/2000	Chu et al.	148	33.1	
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	AF						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
	AG						
	AH						
EXAMINER <div style="font-size: 1.2em; font-family: cursive;">Thain Kane</div>				DATE CONSIDERED <div style="font-size: 1.2em; font-family: cursive;">03/09/2005</div>			
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